

S1D16700

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1. DESCRIPTION

The S1D16700 is a 100 output low-power resistance common (row) driver which is suitable for driving a very high capacity dotmatrix LCD panels upto a duty ratio of 1/300. It is intended to be used in conjunction with the S1D16400 or S1D16006 as a pair.

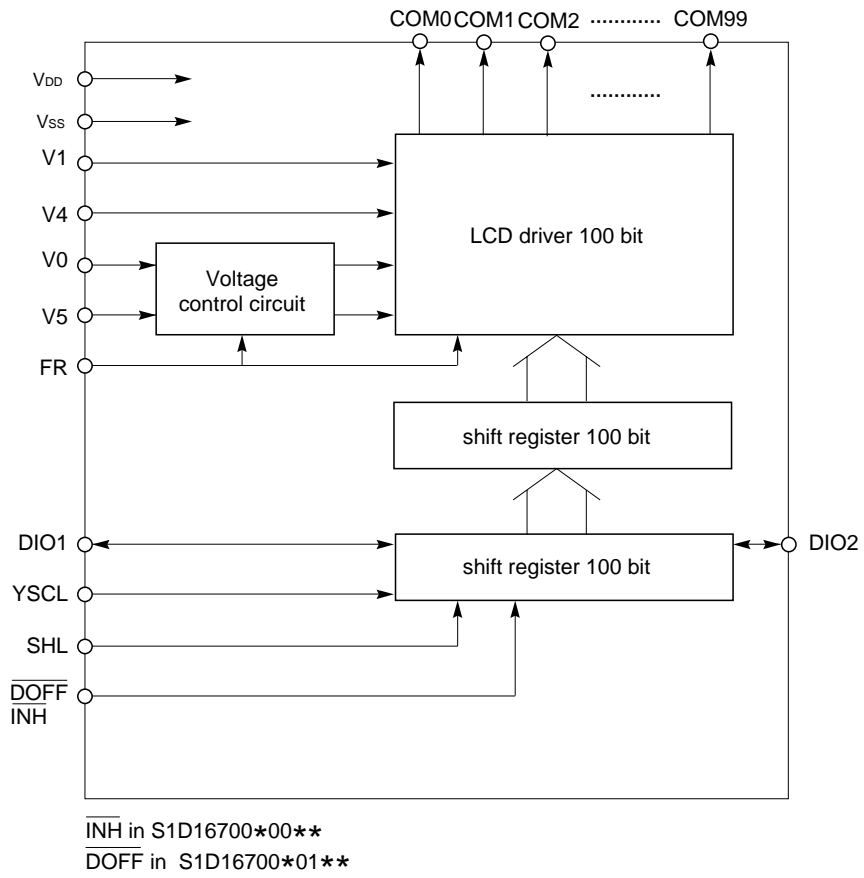
Since the S1D16700 is so designed to drive LCDs over a wide range of voltages, and also the maximum potential V_0 of its LCD drive bias voltages is isolated from V_{DD} to allow the LCD driving bias voltages to be externally generated optionally with a high accuracy, it can cope with a wide range of LCD panels.

Owing to its pad layout which can minimize its PC boards mounting space in addition to its selectable bidirectional driver output sequence and as many as 100 LCD output segments of high pressure resistance and low output impedance, it is possible to obtain the highest driver working efficiency for the 1/200 duty panel. And the S1D16700*01** can display 65 x 132 panel when used as a common driver of RAM built-in driver, S1D15301.

2. FEATURES

- Number of LCD drive output segments: 100
- Common output ON resistance: 700 Ω (Typ.)
- Display duty ratio: 1/64 to 1/300 (Reference)
- Display capacity: Possible to display 640 \times 480 dots when used in combination with S1D 16400D or S1D16006D.
- Selectable pin output shift direction
- No-bias display OFF function (S1D16700*01**)
- Instantaneous display blanking enabled by inhibit function (S1D16700*00**)
- Adjustable offset bias of LCD power to V_{DD} level
- Wide range of LCD drive voltages: -7 V to -28 V (Absolute maximum rated voltage: -30 V)
- Logic system power supply: -2.7 V to -5.5 V
- Shipping pattern
 - S1D16700D00A* (Al pad chip)
 - S1D16700D01A* (Al pad chip)
 - S1D16700D00B* (Au bump chip)
 - S1D16700D01B* (Au bump chip)
 - S1D16700T00A* (TCP)
 - S1D16700T01A* (TCP)
- No radial rays countermeasure taken in designing

3. BLOCK DIAGRAM



4. PIN DESCRIPTION

Pin name	I/O	Function	Number of pins															
COM0 to COM099	O	LCD drive common (row) output The output changes at the YS CL falling edge.	100															
DIO1, DIO2	I/O	100-bit shift register serial data input/output To be set to input or output according to the SHL input The output changes at the YSCL falling edge.	2															
YSCL	I	Serial data shift clock input The scanning data is shifted at the falling edge.	1															
SHL	I	Shift direction selection and DIO pin I/O control input	1															
		<table border="1"> <thead> <tr> <th>SHL</th> <th colspan="2">COM output shift direction</th> <th>DIO1</th> <th>DIO2</th> </tr> </thead> <tbody> <tr> <td>LOW</td> <td>0</td> <td>→ 99</td> <td>Input</td> <td>Output</td> </tr> <tr> <td>HIGH</td> <td>99</td> <td>→ 0</td> <td>Ourput</td> <td>Input</td> </tr> </tbody> </table>		SHL	COM output shift direction		DIO1	DIO2	LOW	0	→ 99	Input	Output	HIGH	99	→ 0	Ourput	Input
		SHL		COM output shift direction		DIO1	DIO2											
LOW	0	→ 99	Input	Output														
HIGH	99	→ 0	Ourput	Input														
$\overline{\text{DOFF}}$	I	LCD display blanking control input When LOW is input, the content of shift register is cleared and all common outputs become the V_0 level instantaneously (S1D16700D01B★).	1															
$(\overline{\text{INH}})$	I	LCD drive display blanking control input When LOW is input, the content of shift register is cleared and all common outputs become the non-select level instantaneously. Common output = V_4 (when FR = LOW) Common output = V_1 (when FR = HIGH) (S1D16700D00B★)	(1)															
FR	I	LCD drive output AC converted signal input	1															
V_{DD} , V_{SS}	Power supply	Logic power supply V_{DD} : 0 V (GND) V_{SS} : -5.0 V	2															
V_0 , V_1 , V_4 , V_5	Power supply	LCD drive power supply V_5 : -7 V to -28 V $V_{DD} \geq V_0 \geq V_1 > V_4 \geq V_5$	4															

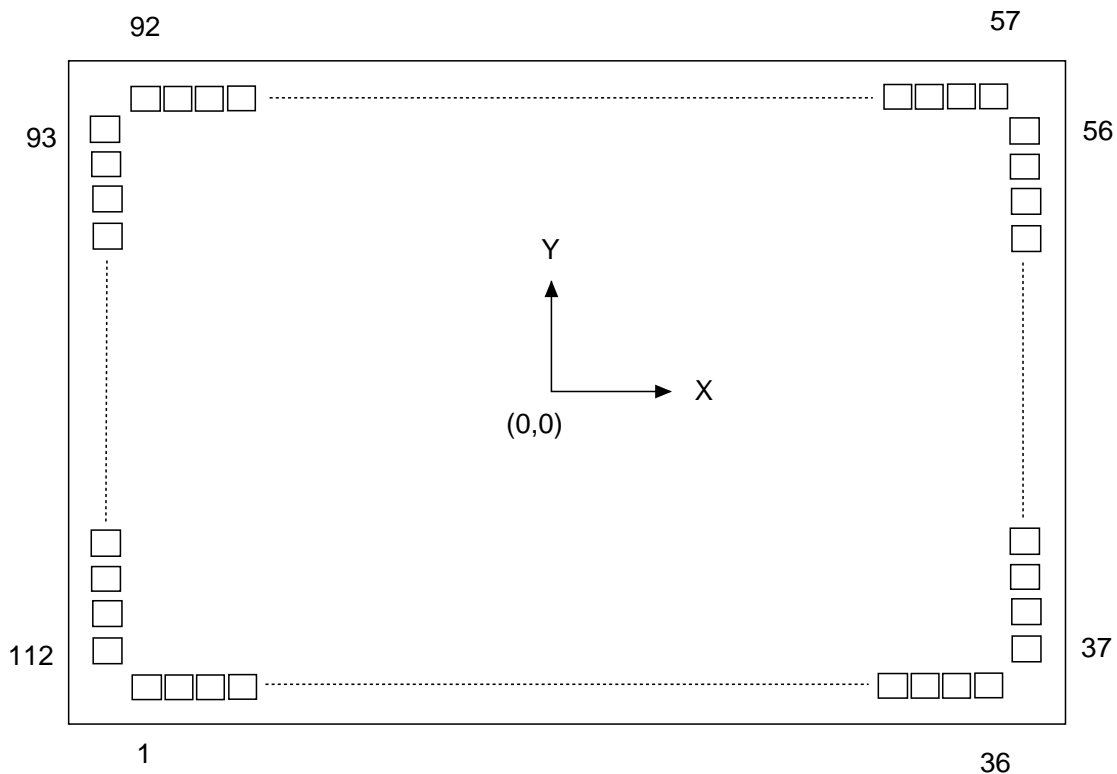
$\overline{\text{INH}}$ for S1D16700*00**

$\overline{\text{DOFF}}$ for S1D16700*01**

Total: 112

5. PAD

• Pad layout



Chip size 5.49mm × 3.03mm
 Chip thickness 525µm (Au-bump die from)
 400µm (Al-Pad die from)

1) Au bump specification reference values

Bump specific : High Quality Au bump
 Bump size : 90µm × 90µm
 Bump height : 17µm ~ 28µm

2) AL Pad specification reference values

Pad Opening : 100µm × 100µm

● Pad center coordinates

PAD		Actual dimensions		PAD		Actual dimensions		PAD		Actual dimensions	
NO.	NAME	X	Y	NO.	NAME	X	Y	NO.	NAME	X	Y
1	COM5	-2187	-1357	41	COM45	2584	-711	81	COM85	-803	1357
2	6	-2058		42	46		-581	82	86	-932	
3	7	-1929		43	47		-452	83	87	-1062	
4	8	-1799		44	48		-323	84	88	-1191	
5	9	-1670		45	49		-194	85	89	-1320	
6	10	-1541		46	50		-65	89	90	-1449	
7	11	-1412		47	51		65	87	91	-1578	
8	12	-1283		48	52		194	88	92	-1708	
9	13	-1153		49	53		323	89	93	-1837	
10	14	-1024		50	54		452	90	94	-1966	
11	15	-895		51	55		581	91	95	-2095	↓
12	16	-766		52	56		711	92	96	-2224	1357
13	17	-637		53	57		840	93	97	-2473	1334
14	18	-507		54	58		969	94	98		1201
15	19	-378		55	59	↓	1098	95	99		1071
16	20	-249		56	60	2584	1231	96	DIO2		941
17	21	-120		57	61	2298	1357	97	$\overline{\text{DOFF}}$		715
18	22	10		58	62	2168		(97)	$\overline{(\text{INH})}$		
19	23	139		59	63	2039		98	FR		585
20	24	268		60	64	1910		99	YSCL		455
21	25	397		61	65	1781		100	SHL		325
22	26	526		62	66	1652		101	V _{DD}		185
23	27	656		63	67	1522		102	V _{SS}		46
24	28	785		64	68	1393		103	V ₀		-112
25	29	914		65	69	1264		104	V ₁		-252
26	30	1043		66	70	1135		105	V ₄		-391
27	31	1172		67	71	1006		106	V ₅		-531
28	32	1302		68	72	876		107	DIO1		-671
29	33	1431		69	73	747		108	COM0		-810
30	34	1560		70	74	618		109	1		-941
31	35	1689		71	75	489		110	2		-1071
32	36	1818		72	76	360		111	3	↓	-1201
33	37	1948		73	77	230		112	4	-2473	-1334
34	38	2077		74	78	101					
35	39	2206	↓	75	79	-28					
36	40	2335	-1357	76	80	-157					
37	41	2584	-1231	77	81	-286					
38	42	2584	-1094	78	82	-416					
39	43	2584	-969	79	83	-545	↓				
40	44	2584	-840	80	84	-674	1357				

PAD No. 97: $\overline{\text{INH}}$ for S1D16700*00**
 $\overline{\text{DOFF}}$ for S1D16700*01**

6. FUNCTIONAL DESCRIPTION

Shift register

This is a bidirectional shift register to transfer common data.

Level shifter

This is a level interface circuit used to convert the signal voltage level from the logic system level to LCD drive level.

LCD driver circuit

This driver outputs the LCD drive voltage.

The relationship among the display blanking signal DOFF, contents of shift register, AC converted signal FR and common output voltage is as shown in the table below:

(S1D16700*01**)

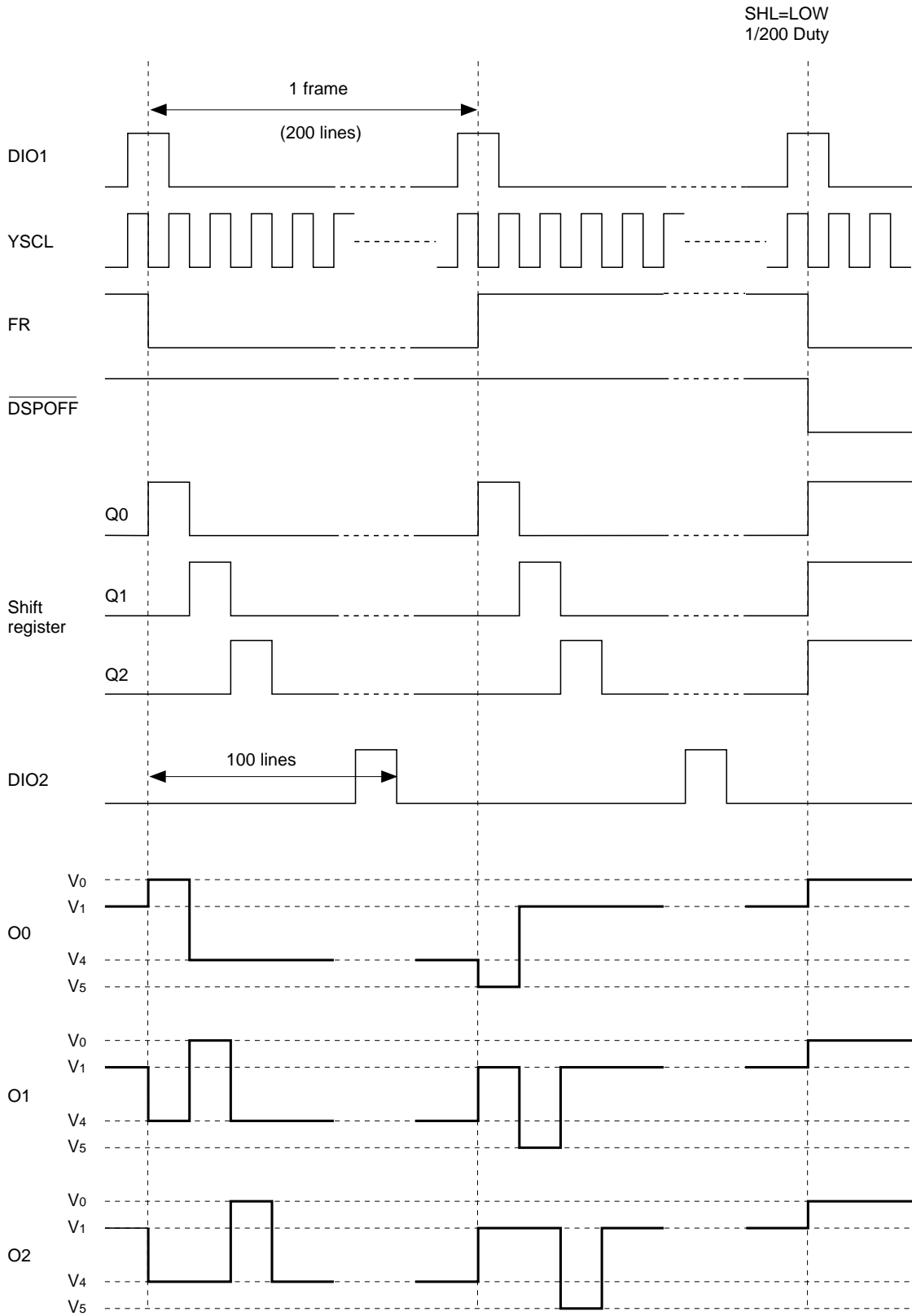
$\overline{\text{DOFF}}$	Contents of shift register	FR	COM output voltage	
HIGH	HIGH	HIGH	V ₅	(Select level)
		LOW	V ₀	
	LOW	HIGH	V ₁	(Non-select level)
		LOW	V ₄	
LOW	Fixed to LOW	–	V ₀	–

The relationship among the display blanking signal INH, contents of the shift register, AC converted signal FR and COM output voltage is as shown in the table below:

(S1D16700*00**)

INH	Contents of shift register	FR	COM output voltage	
HIGH	HIGH	HIGH	V ₅	(Select level)
		LOW	V ₀	
	LOW	HIGH	V ₁	(Non-select level)
		LOW	V ₄	
LOW	Fixed to LOW	HIGH	V ₁	(Non-select level)
		LOW	V ₄	

7. TIMING CHART (S1D16700D01B*)



The V1 or V4 non-select level is output corresponding to the FR in S1D16700D00B* or \overline{INH} =LOW, respectively.

8. ABSOLUTE MAXIMUM RATINGS

V_{DD}=0V

Parameter	Symbol	Rating	Unit
Supply voltage (1)	V _{SS}	-7.0 to +0.3	V
Supply voltage (2)	V ₅	-30.0 to +0.3	V
Supply voltage (3)	V ₀ , V ₁ , V ₄	V ₅ -0.3 to +0.3	V
Input voltage	V _I	V _{SS} -0.3 to +0.3	V
Output voltage	V _O	V _{SS} -0.3 to +0.3	V
Output current (1)	I _O	20	mA
Output current (2)	I _{OCOM}	20	mA
Operating temperature	T _{opr}	-40 to + 85	°C
Storing temperature 1	T _{stg}	-65 to +150	°C

Notes:

1. The voltage of V₀, V₁ and V₄ must always satisfy the condition of V_{DD} ≥ V₀ ≥ V₁ ≥ V₄ ≥ V₅.
2. Floating of the logic system power during while the LCD drive system power is applied, or exceeding V_{SS} = -2.6 V or more can cause permanent damage to the LSI. Functional operation under these conditions is not implied.

Care should be taken to the power supply sequence especially in the system power ON or OFF.

9. ELECTRICAL CHARACTERISTICS

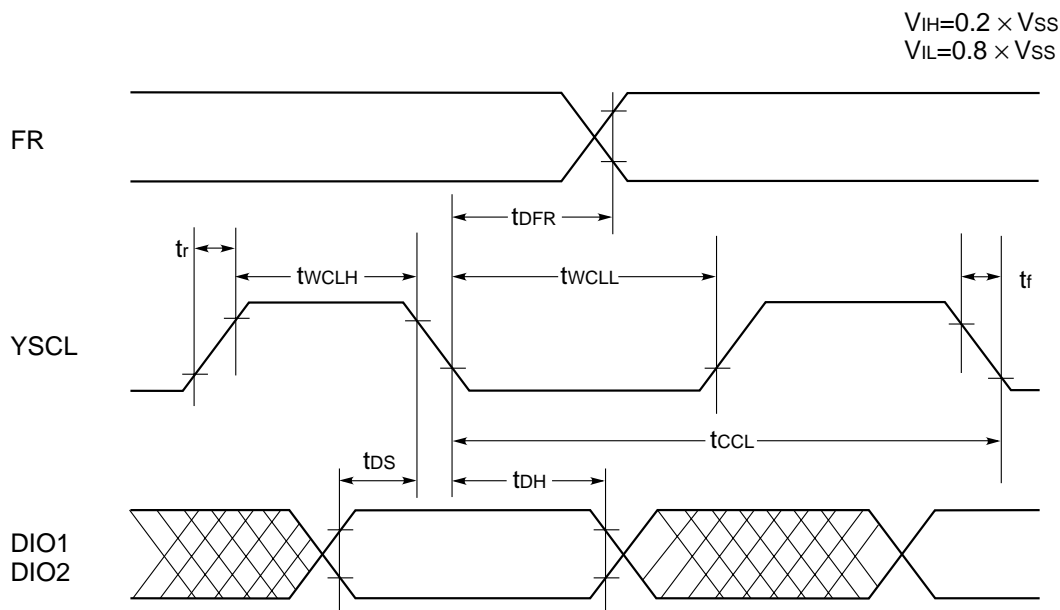
DC characteristics

Unless otherwise specified, $V_{DD} = V_0 = 0V$, $V_{SS} = -5.0V \pm 10\%$, $T_a = -40$ to $85^\circ C$.

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit	Applicable pin
Supply voltage (1)	V_{SS}	–	–5.5	–5.0	–2.7	V	V_{SS}
Recommended operating voltage	V_5	–	–28.0	–	–7.0	V	V_5
Operation enable voltage	V_5	Functional operation	–	–	–7.0	V	V_5
Supply voltage (2)	V_0	Recommended value	–2.5	–	0	V	V_0
Supply voltage (3)	V_1	Recommended value	$2/9 \cdot V_5$	–	V_{DD}	V	V_1
Supply voltage (4)	V_4	Recommended value	V_5	–	$7/9 \cdot V_5$	V	V_4
HIGH input voltage (1)	V_{IH}	$V_{SS} = -2.7V$ to $-5.5V$	$0.2V_{SS}$	–	0	V	DIO1, DIO2, YSCL, SHL, FR
LOW input voltage (1)	V_{IL}		V_{SS}	–	$0.8V_{SS}$	V	
HIGH input voltage (2)	V_{IHT}	$V_{SS} = -2.7V$ to $-5.5V$	$0.2V_{SS}$	–	0	V	\overline{DOFF} , \overline{INH}
LOW input voltage (2)	V_{ILT}		V_{SS}	–	$0.85V_{SS}$	V	
HIGH output voltage	V_{OH}	$I_{OH} = -0.3mA$ $I_{OH} = -0.2mA$ ($V_{SS} = -2.7$ to $-4.5V$)	–0.4	–	0	V	DIO1, DIO2
LOW output voltage	V_{OL}	$I_{OL} = +0.3mA$ $I_{OL} = +0.2mA$ ($V_{SS} = -2.7$ to $-4.5V$)	V_{SS}	–	$V_{SS} + 0.4$	V	
Input leakage current	I_{LI}	$V_{SS} \leq V_{IN} \leq 0V$	–	–	2.0	μA	YSCL, SHL, \overline{DOFF} , \overline{INH} , FR
Input/output leakage current	$I_{L/O}$	$V_{SS} \leq V_{IN} \leq 0V$	–	–	5.0	μA	DIO1, DIO2
Static current	I_{DDS}	$V_5 = -7.0$ to $-28.0V$ $V_{IH} = V_{DD}$, $V_{IL} = V_{SS}$	–	–	25	μA	V_{DD}
Output resistance	R_{COM}	$\Delta V_{ON} = 0.5V$ $V_5 = -20.0V$ When the V_1 , V_4 , V_0 or V_5 level is output	–	0.70	1.40	$k\Omega$	COM0~COM99
Average operating current consumption (1)	I_{SS1}	$V_{SS} = -5.0V$, $V_{IH} = V_{DD}$, $V_{IL} = V_{SS}$, $f_{YSCL} = 12KHz$, Frame frequency = 60Hz Input data; "H" at no load every 1/200 duty Other conditions are the same as $V_{SS} = -3.0V$	–	7	15	μA	V_{SS}
			–	5	10		
Average operating current consumption (2)	I_{SS2}	$V_{SS} = -5.0V$, $V_1 = -2.0V$, $V_4 = -18.0V$, $V_5 = -20.0V$ Other conditions are the same as in the item of I_{SS1} .	–	7	15	μA	V_5
Input pin capacitance	C_i	$T_a = 25^\circ C$	–	–	8	pF	YSCL, SHL, \overline{DOFF} , \overline{INH} , FR
Input/output pin capacitance	$C_{I/O}$		–	–	15	pF	DIO1, DIO2

AC Characteristics

Input timing characteristics



Unless otherwise specified $V_{SS}=-5.0V \pm 10\%$, $T_a=-40$ to $85^\circ C$

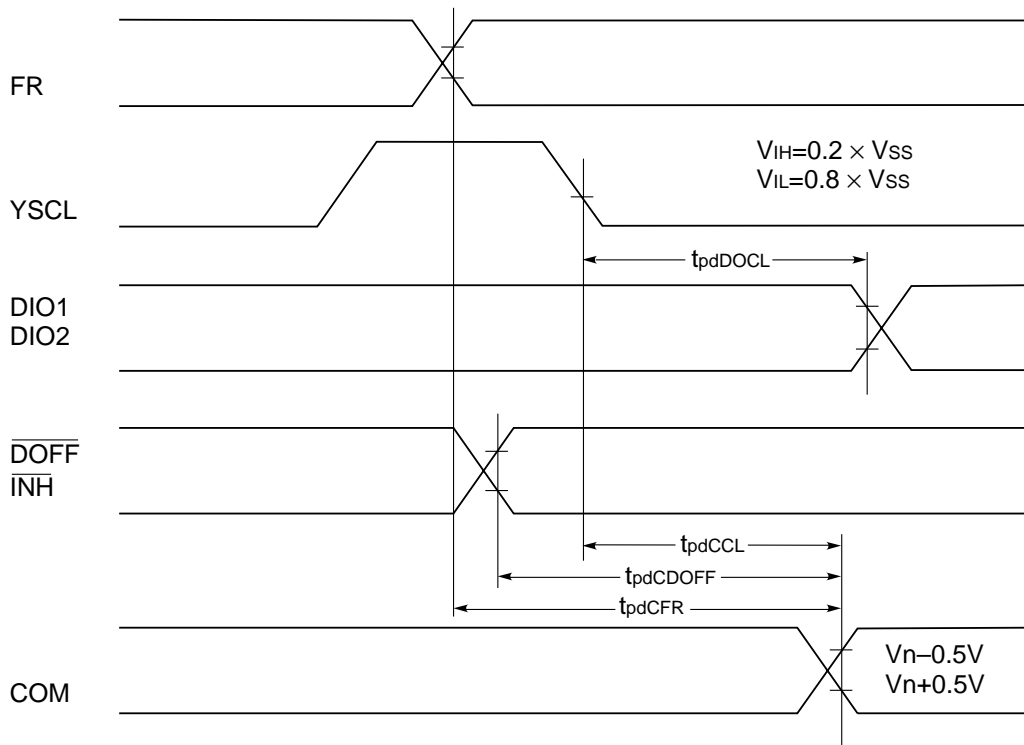
Parameter	Symbol	Condition	Min.	Max.	Unit
Input signal rise time	t_r	—	—	50	ns
Input signal fall time	t_f	—	—	50	ns
YSCL period	t_{cCL}	—	500	—	ns
YSCL HIGH pulsewidth	t_{wCLH}	—	70	—	ns
YSCL LOW pulsewidth	t_{wCLL}	—	330	—	ns
Data setup time	t_{DS}	—	100	—	ns
Data hold time	t_{DH}	—	10	—	ns
Allowable FR delay time	t_{DFR}	—	-500	500	ns

Unless otherwise specified $V_{SS}=-2.7V$ to $-4.5V$, $T_a=-40$ to $85^\circ C$

Parameter	Symbol	Condition	Min.	Max.	Unit
Input signal rise time	t_r	—	—	50	ns
Input signal fall time	t_f	—	—	50	ns
YSCL period	t_{cCL}	—	1000	—	ns
YSCL HIGH pulsewidth	t_{wCLH}	—	160	—	ns
YSCL LOW pulsewidth	t_{wCLL}	—	330	—	ns
Data setup time	t_{DS}	—	200	—	ns
Data hold time	t_{DH}	—	10	—	ns
Allowable FR delay time	t_{DFR}	—	-500	500	ns

The standard applicable to t_{cCL} , t_{wCLH} , t_{wCLL} and t_{DS} when $V_{SS} = -2.4 V$ shall be 1.3 times of that applies when $V_{SS} = -2.7V$ to $-4.5V$.

Output timing characteristics



Unless otherwise specified $V_{SS}=-5.0V \pm 10\%$, $T_a=-40$ to $85^\circ C$

Parament	Symbol	Condition	Min.	Max.	Unit
(YSCL - fall to DIO) delay time	t_{pdDOCL}	$CL=15pF$	30	300	ns
(YSCL - fall to COM output) delay time	t_{pdCCL}	$V_5=-7.0$ to $-28.0V$ $CL=100pF$	-	3.0	μs
(DOFF to COM output) delay time	$t_{pdCDOFF}$				
(INH to COM output) delay time	t_{pdCINH}				
(FR to COM output) delay time	t_{pdCFR}		-	3.0	μs

Unless otherwise specified $V_{SS}=-2.7V$ to $-4.5V$, $T_a=-40$ to $85^\circ C$

Parament	Symbol	Condition	Min.	Max.	Unit
(YSCL - fall to DIO) delay time	t_{pdDOCL}	$CL=15pF$	60	600	ns
(YSCL - fall to COM output) delay time	t_{pdCCL}	$V_5=-7.0$ to $-28.0V$ $CL=100pF$	-	3.0	μs
(DOFF to COM output) delay time	$t_{pdCDOFF}$				
(INH to COM output) delay time	t_{pdCINH}				
(FR to COM output) delay time	t_{pdCFR}		-	3.0	μs

The standard applicable at $V_{SS} = -2.4V$ shall be the same as that employed when $V_{SS} = -2.7V$ to $-4.5V$.

10. LCD DRIVE POWER

Each voltage level forming method

To obtain each voltage level for LCD driving, it is the most simple to divide the resistance of potential as shown in the connection example. On the other hand, to obtain a high quality display, it is necessary to raise the accuracy and constancy of each voltage level and to set the divided resistance value as low as possible in the range of system power capacity.

Especially when a low-power LCD driving is required, set the divided resistance to a higher value and drive the LCD with a voltage follower by means of operational amplifier instead. In taking into consideration of a case where the operational amplifier is employed, the maximum potential level V_0 for LCD driving has been isolated from the VDD pin.

When the potential of V_0 lowers than that of VDD and the potential difference between the two becomes larger, however, the capacity of LCD drive output driver lowers. To avoid it, use the system with the potential difference of 0 V to 2.5 V between V_0 and VDD.

When no operational amplifier is used, connect V_0 and VDD pins.

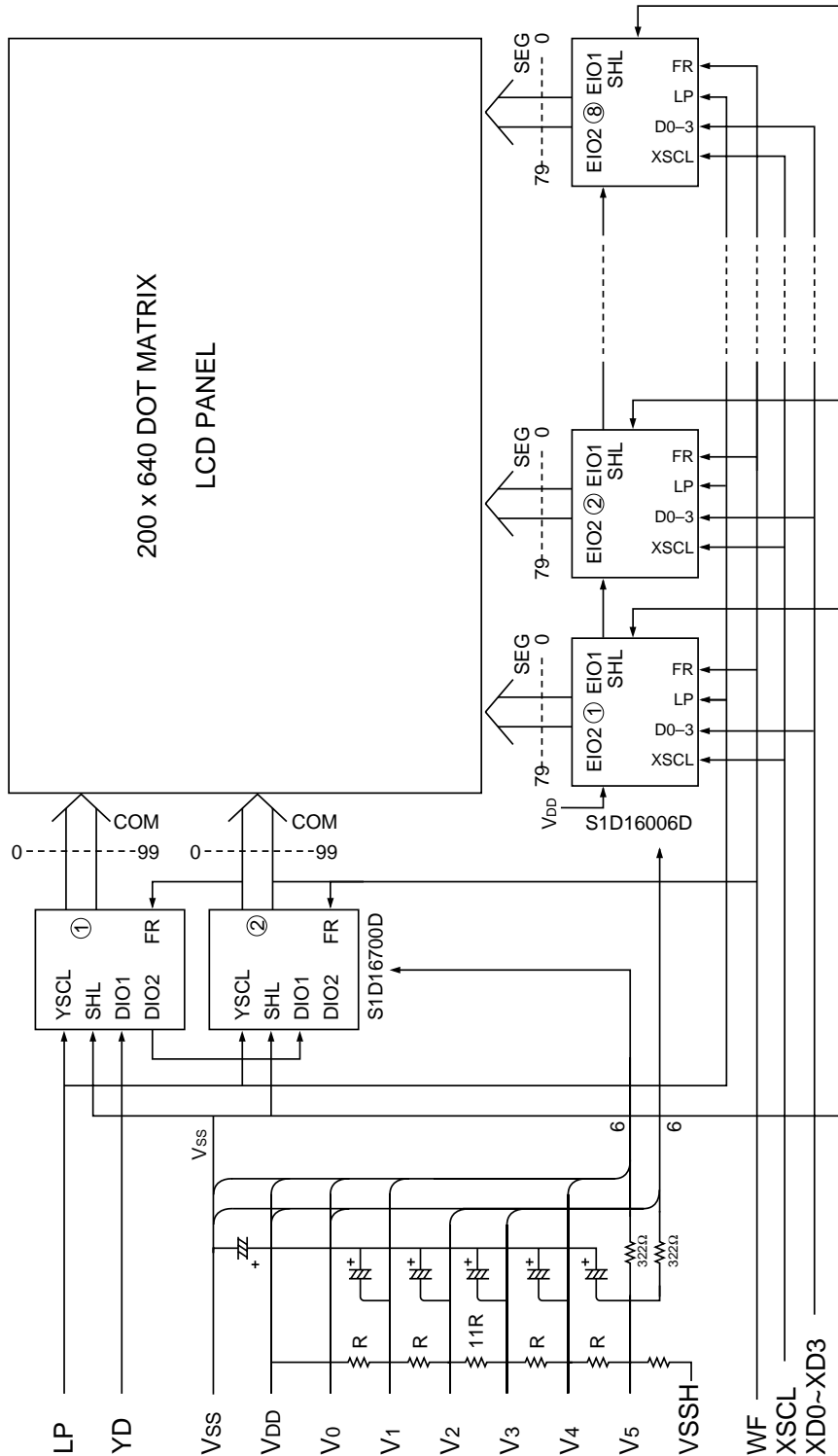
Note in power ON/OFF

Since this LSI is high in the voltage of LCD driving system, when a high voltage is applied to the LCD driving system with the logic system power supply kept floating, an overcurrent flows and LSI breaks down in some cases.

Be sure to follow the power ON/OFF sequence as shown below:

At power ON ... Logic system ON → LCD driving system ON or simultaneous ON of the both
At power OFF ... LCD driving system OFF → Logic system OFF or simultaneous OFF of the both

11. CONNECT EXAMPLE



Note *1 It must be provided as the protective resistor against overcurrent. Also, the bypass capacitor (0.01 μ F) for noise suppression must be provided near to Vss and V5 terminals on each LSI.